Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8519	((257/52) or (257/57) or (257/66) or (257/72) or (257/72) or (257/327) or (257/344) or (257/347) or (257/382) or (257/383) or (257/384) or (257/624) or (257/625) or (257/e21.561) or (257/e21.545) or (257/e21.32) or (257/e27.112) or (257/e29.156)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/27 11:24
L2	254	L1 and "SOI" and contact near4 resistance and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/27 11:27
L3	123	L1 and "SOI" and contact near4 shape	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/27 11:27
S1	3	"749273".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/19 19:55
S2	167	((257/624) or (257/625)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/17 09:19
S3	1402	((257/327) or (257/382) or (257/383) or (257/384)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/18 17:02
S4	315	S3 and contact adj resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 17:03
S5	7	(US-20050040472-$).did. or (US-6515340-$ or US-6515348-$ or US-6087706-$ or US-6040589-$ or US-5191397-$ or US-5113234-$).did.	US-PGPUB; USPAT	OR	OFF	2005/03/17 12:16
S6	742	(thin adj film adj transistor tft).ti, ab,clm. and (active adj (layer film) semiconductor adj thin adj film) near5 (thick thickness)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:17

S7	0	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near5 (thick thickness) ".ANG.")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:18
S8	0	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 ".ANG.")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:18
S9	63	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 (".ANG." ".mu.m" Angstrom))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:29
S10	33	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 (".ANG." ".mu.m" Angstrom)) and (thick thickness). ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:31
S11	4	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 (".ANG." ".mu.m" Angstrom)) and (thick thickness) near4 active.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:15
S12	6	"665204".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:17
S13	1	InP near4 buffer and buffer near4 graded and graded near4 InGaAsP	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:18
S14	3	InP near8 buffer and buffer near8 graded and graded near8 InGaAsP	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:19

S15	5	InP near16 buffer and buffer near16 graded and graded near16 InGaAsP and (photodiode photodetect$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:20
S16	8	(US-20050040472-$).did. or (US-5113234-$ or US-5191397-$ or US-6040589-$ or US-6087706-$ or US-6515340-$ or US-6515348-$).did. or (EP-235827-$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 15:00
S17	148	(SiGe silicon adj germanium SiC silicon adj carbide) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 16:00
S18	67	(SiGe silicon adj germanium and SiC silicon adj carbide) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 09:12
S19	5	((SiGe silicon adj germanium) and (SiC silicon adj carbide)) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 15:15
S20	0	wo-0282526$-$.did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 15:15
S21	0	wo-0282526$-$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 15:15
S22	1	wo-200282526$-$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 15:17
S23	2	jp-2003046068$-$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 15:17
S24	43	(ONO silicon adj oxynitride) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 16:05

S25	9	(US-20020014625-$ or US-20050040472-$).did. or (US-5113234-$ or US-5191397-$ or US-6040589-$ or US-6087706-$ or US-6515340-$ or US-6515348-$).did. or (EP-235827-$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 09:01
S26	1	S25 and (buried adj oxide BOx)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 09:02
S27	11	(buried adj oxide BOx) near6 insulating adj (layer film) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 09:17
S28	519	(buried adj oxide SIMOx) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 09:17
S29	179	(buried adj oxide SIMOx) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft).ti, ab,clm.	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 09:19
S30	66	(buried adj oxide SIMOx) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft).ti, ab,clm. and buried	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 10:31
S31	0	(buried adj oxide SIMOx) near3 (preferabl$1 advantage) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft).ti, ab,clm. and buried	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 10:32
S32	266	(buried adj oxide SIMOx) near12 (preferabl$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:32
S33	10	(buried adj oxide SIMOx) near12 (preferabl$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:42
S34	1	(buried adj oxide SIMOx) near12 (preferabl$1 advantage) near12 wafer adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:47

S35	2	("6335231").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 10:45
S36	0	(buried adj oxide) near12 (preferabl$1 advantage) near12 wafer adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S37	183	(buried adj oxide) near12 (preferabl$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S38	104	(buried adj oxide) near6 (preferabl$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S39	75	(buried adj oxide) near4 (preferabl$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S40	58	(buried adj oxide) near3 (preferabl$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S41	0	(buried adj oxide) near3 (preferabl$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S42	2	(buried adj oxide) near6 (preferabl$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:49

S43	5	(buried adj oxide) near8 (preferabl$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:51
S44	2283	pixel adj electrode near6 (contact$3 connect$3 abut$4) near6 (insulating buried oxide dioxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:52
S45	2045	pixel adj electrode near6 (contact$3 connect$3 abut$4) near6 (insulating buried adj oxide dioxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:52
S46	785	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating buried adj oxide dioxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:53
S47	669	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating buried adj oxide dioxide) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:54
S48	415	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating buried adj oxide dioxide) and thin adj film adj transistor.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:54
S49	0	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (buried adj oxide) and thin adj film adj transistor.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:54
S50	467	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating adj (film layer)) and thin adj film adj transistor.ti, ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:55

S51	9	(US-20020014625-$ or US-20050040472-$).did. or (US-5113234-$ or US-5191397-$ or US-6040589-$ or US-6087706-$ or US-6515340-$ or US-6515348-$).did. or (EP-235827-$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 11:33
S52	1	S51 and furuta.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 11:33
S53	1	S51 and furuta.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 14:20
S54	122	silicon adj oxynitride near3 dielectric adj constant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 14:20
S55	68	silicon adj oxynitride near2 dielectric adj constant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 15:39
S56	3	("6040589").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 15:39
S57	1	S56 and interconnect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 15:39
S58	2631	((257/52) or (257/57) or (257/66) or (257/72)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/18 17:02
S59	237	S58 and contact adj resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 17:03
S60	1	wo-200282526$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/19 17:15

S61	1	wo-200282526$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/19 17:16
S62	1	wo-200282526$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/19 17:16
S63	2	morita.in. and miyake.in. and @pd="20021017"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/19 17:17
S64	3	("6040589").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/19 20:36
S65	2	("5113234").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/19 20:48
S66	9854	((257/52) or (257/57) or (257/66) or (257/72) or (257/72) or (257/327) or (257/347) or (257/382) or (257/383) or (257/384) or (257/624) or (257/625) or (257/e21.561) or (257/e21.545) or (257/e21.32) or (257/e27.112)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 08:49
S67	7564	((257/52) or (257/57) or (257/66) or (257/72) or (257/72) or (257/327) or (257/347) or (257/382) or (257/383) or (257/384) or (257/624) or (257/625) or (257/e21.561) or (257/e21.545) or (257/e21.32) or (257/e27.112)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/19 20:51
S68	1	S67 and contact adj resistance and silicide adj contact and wrap$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/19 20:53
S69	35	S67 and contact adj resistance and silicide adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/19 21:01

S70	284	(257/e29.156).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/19 21:01
S71	7812	((257/52) or (257/57) or (257/66) or (257/72) or (257/72) or (257/327) or (257/347) or (257/382) or (257/383) or (257/384) or (257/624) or (257/625) or (257/e21.561) or (257/e21.545) or (257/e21.32) or (257/e27.112) or (257/e29.156)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/20 15:39
S72	0	S71 and resistance near2 contact and wrap$4 near8 (contact silicide WN TiN TaN cobalt adj silicide nickel adj silicide salicide) near8 (drain adj region source adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 08:55
S73	0	S71 and (reduce reduction improve improvement decrease lower lowering smaller) near4 resistance near2 contact and wrap$4 near8 (contact silicide WN TiN TaN cobalt adj silicide nickel adj silicide salicide) near8 (drain adj region source adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 08:56
S74	257	S71 and (reduce reduction improve improvement decrease lower lowering smaller) near4 resistance near2 contact and (contact silicide WN TiN TaN cobalt adj silicide nickel adj silicide salicide) near8 (drain adj region source adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 10:32
S75	2664	S71 and (contact silicide WN TiN TaN cobalt adj silicide nickel adj silicide salicide) near8 (drain adj region source adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 10:33
S76	1177	S71 and (contact silicide WN TiN TaN cobalt adj silicide nickel adj silicide salicide) near8 (drain adj region source adj region) same "between"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 10:34
S77	2166	S71 and (contact silicide WN TiN TaN cobalt adj silicide nickel adj silicide salicide) near4 (drain adj region source adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 10:58

S78	0	S71 and (contact silicide WN TiN TaN cobalt adj silicide nickel adj silicide salicide) near4 (drain adj region source adj region) and minimum adj contact adj area	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 10:59
S79	232	S71 and (contact silicide WN TiN TaN cobalt adj silicide nickel adj silicide salicide) near4 (drain adj region source adj region) and contact adj area	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 10:59
S80	25	"SOI".ti. and silicide.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 15:19
S81	1451	((257/327) or (257/382) or (257/383) or (257/384)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/20 15:27
S82	879	(257/344).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/20 15:27
S83	1	"5384485".PN.	USPAT; USOCR	OR	OFF	2005/06/20 15:32
S84	1	"5962898".PN.	USPAT; USOCR	OR	OFF	2005/06/20 15:32
S85	1	"6242776".PN.	USPAT; USOCR	OR	OFF	2005/06/20 15:33
S86	8487	((257/52) or (257/57) or (257/66) or (257/72) or (257/72) or (257/327) or (257/344) or (257/347) or (257/382) or (257/383) or (257/384) or (257/624) or (257/625) or (257/e21.561) or (257/e21.545) or (257/e21.32) or (257/e27.112) or (257/e29.156)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/23 16:31
S87	220	S86 and "SOI".ti,ab,clm. and silicide.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 15:40
S88	223	S86 and "SOI".ti,ab,clm. and silicide.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:32

S89	8519	((257/52) or (257/57) or (257/66) or (257/72) or (257/72) or (257/327) or (257/344) or (257/347) or (257/382) or (257/383) or (257/384) or (257/624) or (257/625) or (257/e21.561) or (257/e21.545) or (257/e21.32) or (257/e27.112) or (257/e29.156)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/23 16:31
S90	223	S89 and "SOI".ti,ab,clm. and silicide.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:31
S91	8519	((257/52) or (257/57) or (257/66) or (257/72) or (257/72) or (257/327) or (257/344) or (257/347) or (257/382) or (257/383) or (257/384) or (257/624) or (257/625) or (257/e21.561) or (257/e21.545) or (257/e21.32) or (257/e27.112) or (257/e29.156)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/23 16:32
S92	223	S91 and "SOI".ti,ab,clm. and silicide.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:49
S93	0	("331144.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/23 16:49